## Lars Rebohle

List of Publications by Year in descending order

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687363 677142 44 546 13 22 citations h-index g-index papers 53 53 53 684 docs citations times ranked citing authors all docs

#	Article	IF	Citations
1	Room-temperature short-wavelength infrared Si photodetector. Scientific Reports, 2017, 7, 43688.	3.3	79
2	A review of thermal processing in the subsecond range: semiconductors and beyond. Semiconductor Science and Technology, 2016, 31, 103001.	2.0	70
3	Ultra-doped n-type germanium thin films for sensing in the mid-infrared. Scientific Reports, 2016, 6, 27643.	3.3	64
4	Self-Driven Broadband Photodetectors Based on MoSe <sub>2</sub> /FePS <sub>3</sub> van der Waals n–p Type-II Heterostructures. ACS Applied Materials & Interfaces, 2022, 14, 11927-11936.	8.0	35
5	n-InAs Nanopyramids Fully Integrated into Silicon. Nano Letters, 2011, 11, 2814-2818.	9.1	23
6	Enhanced Trion Emission in Monolayer MoSe <sub>2</sub> by Constructing a Typeâ€I Van Der Waals Heterostructure. Advanced Functional Materials, 2021, 31, 2104960.	14.9	21
7	Millisecond thermal processing using flash lamps for the advancement of thin layers and functional coatings. Surface and Coatings Technology, 2017, 314, 169-176.	4.8	20
8	Siliconâ€Based Intermediateâ€Band Infrared Photodetector Realized by Te Hyperdoping. Advanced Optical Materials, 2021, 9, 2001546.	7.3	19
9	On the insulator-to-metal transition in titanium-implanted silicon. Scientific Reports, 2018, 8, 4164. Strain and Band-Gap Engineering in <mml:math <="" td="" xmlns:mml="http://www.w3.org/1998/Math/MathML"><td>3.3</td><td>17</td></mml:math>	3.3	17
10	display="inline" overflow="scroll"> <mml:mi>Ge</mml:mi> - <mml:math display="inline" overflow="scroll" xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mi>Sn</mml:mi></mml:math> Alloys via <mml:math <="" display="inline" td="" xmlns:mml="http://www.w3.org/1998/Math/MathML"><td>3.8</td><td>17</td></mml:math>	3.8	17
11	overflow="scroll"> <mml:mrow><mml:mrow><mml:mi mathyariant="normal"&gt;PIlla ("V semiconductor nanocrystal formation in silicon nanowires via liquid-phase epitaxy. Nano Research, 2014, 7, 1769-1776.</mml:mi </mml:mrow></mml:mrow>	10.4	15
12	Blacklight sintering of ceramics. Materials Horizons, 2022, 9, 1717-1726.	12.2	15
13	Rare-Earth Implanted MOS Devices for Silicon Photonics. Springer Series in Materials Science, 2010, , .	0.6	14
14	Flash-Enhanced Atomic Layer Deposition: Basics, Opportunities, Review, and Principal Studies on the Flash-Enhanced Growth of Thin Films. ECS Journal of Solid State Science and Technology, 2015, 4, P277-P287.	1.8	13
15	III-V/Si on silicon-on-insulator platform for hybrid nanoelectronics. Journal of Applied Physics, 2014, 115, .	2.5	12
16	CMOS ompatible Controlled Hyperdoping of Silicon Nanowires. Advanced Materials Interfaces, 2018, 5, 1800101.	3.7	11
17	Flash Lamp Annealing. Springer Series in Materials Science, 2019, , .	0.6	10
18	Phase Selection in Mn–Si Alloys by Fast Solidâ€6tate Reaction with Enhanced Skyrmion Stability. Advanced Functional Materials, 2021, 31, 2009723.	14.9	9

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19	Mid- and far-infrared localized surface plasmon resonances in chalcogen-hyperdoped silicon. Nanoscale, 2022, 14, 2826-2836.	5.6	9
20	Liquid phase epitaxy of binary Ill–V nanocrystals in thin Si layers triggered by ion implantation and flash lamp annealing. Journal of Applied Physics, 2015, 117, 175307.	2.5	7
21	Superconductivity in single-crystalline aluminum- and gallium-hyperdoped germanium. Physical Review Materials, 2019, 3, .	2.4	7
22	The formation of near surface SiGe layers with combined highâ€dose ion implantation and flashâ€lamp annealing. Physica Status Solidi C: Current Topics in Solid State Physics, 2011, 8, 960-963.	0.8	6
23	Formation of regularly arranged large grain silicon islands by using embedded micro mirrors in the flash crystallization of amorphous silicon. Journal of Applied Physics, 2014, 115, 034301.	2.5	5
24	Ill–V nanocrystal formation in ion-implanted Ge and Si via liquid phase epitaxy during short-time flash lamp annealing. Materials Science in Semiconductor Processing, 2016, 42, 166-169.	4.0	5
25	Electrical Characterization of Germanium Nanowires Using a Symmetric Hall Bar Configuration: Size and Shape Dependence. Nanomaterials, 2021, 11, 2917.	4.1	5
26	Controlled immobilization of His-tagged proteins for protein-ligand interaction experiments using Ni2+-NTA layer on glass surfaces. Clinical Hemorheology and Microcirculation, 2016, 61, 523-539.	1.7	4
27	Evaluation of Nanoparticle Inks on Flexible and Stretchable Substrates for Biocompatible Application. , $2018,  ,  .$		4
28	The Technology of Flash Lamp Annealing. Springer Series in Materials Science, 2019, , 15-70.	0.6	4
29	Dissolution of donor-vacancy clusters in heavily doped n-type germanium. New Journal of Physics, 2020, 22, 123036.	2.9	4
30	Controlled Silicidation of Silicon Nanowires Using Flash Lamp Annealing. Langmuir, 2021, , .	3.5	4
31	Formation of In <i><sub>x</sub></i> Ga <sub>1â^'<i>x</i></sub> As nanocrystals in thin Si layers by ion implantation and flash lamp annealing. New Journal of Physics, 2017, 19, 063019.	2.9	3
32	Microstructure and charge trapping in ZrO2- and Si3N4-based superlattice layer systems with Ge nanoparticles. Thin Solid Films, 2018, 645, 124-128.	1.8	3
33	Formation of Thin NiGe Films by Magnetron Sputtering and Flash Lamp Annealing. Nanomaterials, 2020, 10, 648.	4.1	3
34	Local Formation of InAs Nanocrystals in Si by Masked Ion Implantation and Flash Lamp Annealing. Physica Status Solidi C: Current Topics in Solid State Physics, 2017, 14, 1700188.	0.8	3
35	B20–MnSi films grown on Si(100) substrates with magnetic skyrmion signature. Materials Today Physics, 2021, 21, 100541.	6.0	2
36	Deposition of silicon oxide films on silicon using HelixJet - an atmospheric-pressure plasma jet process below 100°C. Thin Solid Films, 2022, 753, 139257.	1.8	2

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#	Article	IF	CITATIONS
37	Evidence for self-organized formation of logarithmic spirals during explosive crystallization of amorphous Ge:Mn layers. Journal of Applied Physics, 2017, 121, 184901.	2.5	1
38	Visible photoluminescence from Ge+-ion-implanted SiO x N y annealed under hydrostatic pressure. , 2001, 4413, 237.		0
39	Fabrication and evaluation of efficient light emitters comprising nanocluster-rich SiO 2 layers. , 2004, , .		O
40	<title>Nanocluster-rich silicon dioxide layers: electroluminescence and charge trapping $<$ /title>. , 2004, , .		0
41	Sensitization of the Blue-green Electroluminescence by Gadolinium Coupled to Si Nanocluster Embedded in a SiO2 Matrix. Medziagotyra, 2013, 19, .	0.2	0
42	Beyond Semiconductors. Springer Series in Materials Science, 2019, , 233-282.	0.6	0
43	Process Management. Springer Series in Materials Science, 2019, , 71-129.	0.6	0
44	Semiconductor Applications. Springer Series in Materials Science, 2019, , 131-232.	0.6	0